

High Voltage Transistors

NPN Silicon

MMBT5550L, MMBT5551L

Features

- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

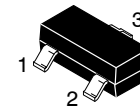
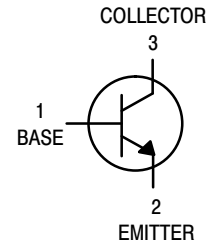
Rating	Symbol	Value	Unit
Collector – Emitter Voltage MMBT5550 MMBT5551	V_{CEO}	140 160	Vdc
Collector – Base Voltage MMBT5550 MMBT5551	V_{CBO}	160 180	Vdc
Emitter – Base Voltage	V_{EBO}	6.0	Vdc
Collector Current – Continuous	I_C	600	mA dc
Electrostatic Discharge Human Body Model Machine Model	ESD	> 8000 > 400	V

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) @ $T_A = 25^\circ\text{C}$ Derate Above 25°C	P_D	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C/W}$
Total Device Dissipation Alumina Substrate (Note 2) @ $T_A = 25^\circ\text{C}$ Derate Above 25°C	P_D	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C/W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

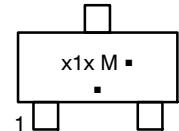
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- FR-5 = $1.0 \times 0.75 \times 0.062$ in.
- Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.



SOT-23 (TO-236)
CASE 318
STYLE 6

MARKING DIAGRAM



x1x = Device Code
M1F = MMBT5550LT
G1 = MMBT5551LT
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBT5550LT1G, NSVMMBT5550LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBT5550LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
MMBT5551LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SMMBT5551LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBT5551LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
SMMBT5551LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MMBT5550L, MMBT5551L

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage (Note 3) (I _C = 1.0 mA, I _E = 0)	MMBT5550 MMBT5551	V _{(BR)CEO}	140 160	– –	Vdc
Collector – Base Breakdown Voltage (I _C = 100 μA, I _E = 0)	MMBT5550 MMBT5551	V _{(BR)CBO}	160 180	– –	Vdc
Emitter – Base Breakdown Voltage (I _E = 10 μA, I _C = 0)		V _{(BR)EBO}	6.0	–	Vdc
Collector Cutoff Current (V _{CB} = 100 Vdc, I _E = 0) (V _{CB} = 120 Vdc, I _E = 0) (V _{CB} = 100 Vdc, I _E = 0, T _A = 100°C) (V _{CB} = 120 Vdc, I _E = 0, T _A = 100°C)	MMBT5550 MMBT5551 MMBT5550 MMBT5551	I _{CBO}	– – – –	100 50 100 50	nA μA
Emitter Cutoff Current (V _{EB} = 4.0 Vdc, I _C = 0)		I _{EBO}	–	50	nA
ON CHARACTERISTICS					
DC Current Gain (I _C = 1.0 mA, V _{CE} = 5.0 Vdc) (I _C = 10 mA, V _{CE} = 5.0 Vdc) (I _C = 50 mA, V _{CE} = 5.0 Vdc)	MMBT5550 MMBT5551 MMBT5550 MMBT5551 MMBT5550 MMBT5551	h _{FE}	60 80 60 80 20 30	– – 250 250 – –	–
Collector – Emitter Saturation Voltage (I _C = 10 mA, I _B = 1.0 mA) (I _C = 50 mA, I _B = 5.0 mA)	Both Types MMBT5550 MMBT5551	V _{CE(sat)}	– – –	0.15 0.25 0.20	Vdc
Base – Emitter Saturation Voltage (I _C = 10 mA, I _B = 1.0 mA) (I _C = 50 mA, I _B = 5.0 mA)	Both Types MMBT5550 MMBT5551	V _{BE(sat)}	– – –	1.0 1.2 1.0	Vdc
Collector Emitter Cut-off (V _{CB} = 10 V) (V _{CB} = 75 V)	Both Types	I _{CES}	– –	50 100	nA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2.0%.

MMBT5550L, MMBT5551L

TYPICAL CHARACTERISTICS

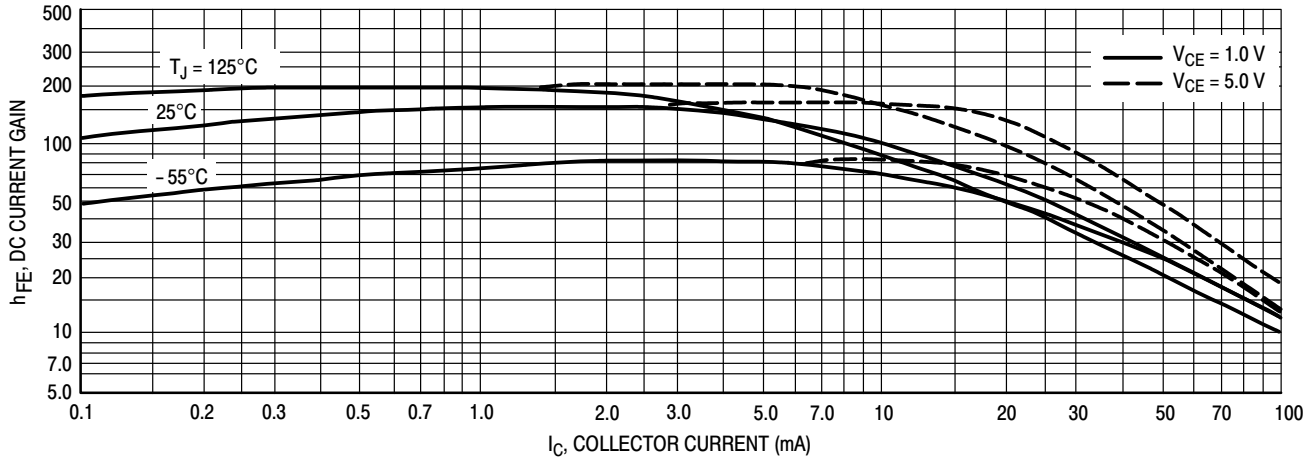


Figure 1. DC Current Gain

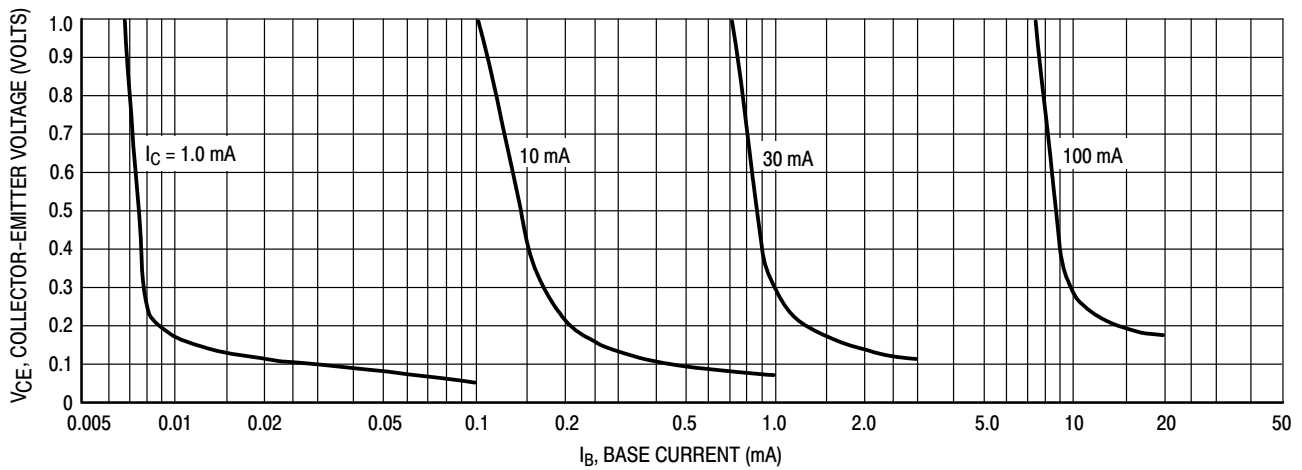


Figure 2. Collector Saturation Region

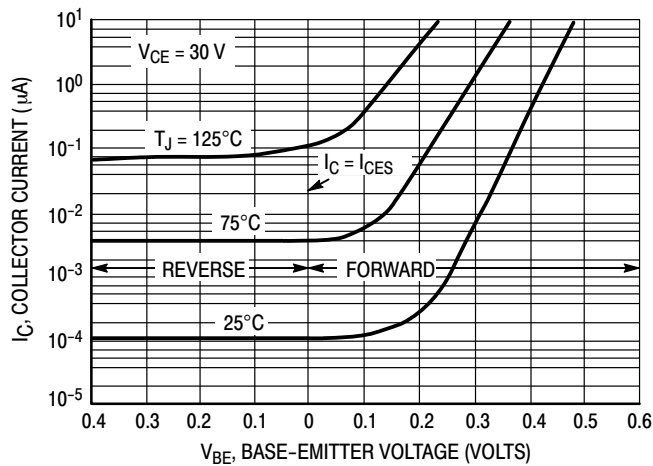


Figure 3. Collector Cut-Off Region

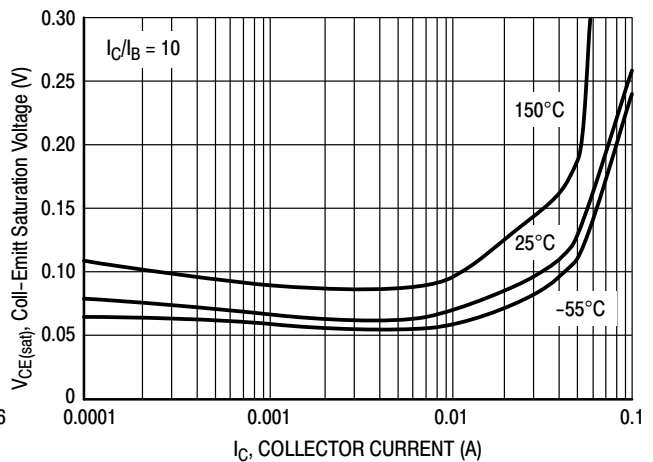


Figure 4. $V_{CE(sat)}$

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TYPICAL CHARACTERISTICS

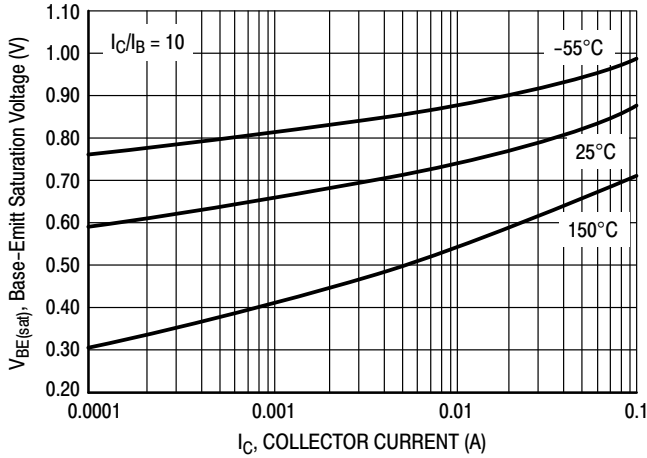


Figure 5. $V_{BE(sat)}$

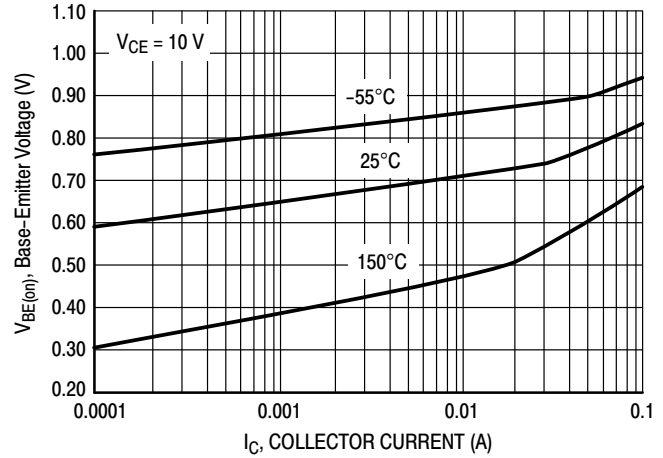


Figure 6. $V_{BE(on)}$

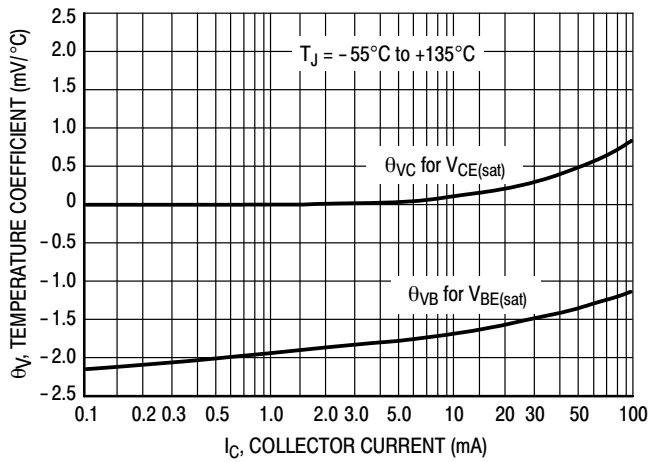


Figure 7. Temperature Coefficients

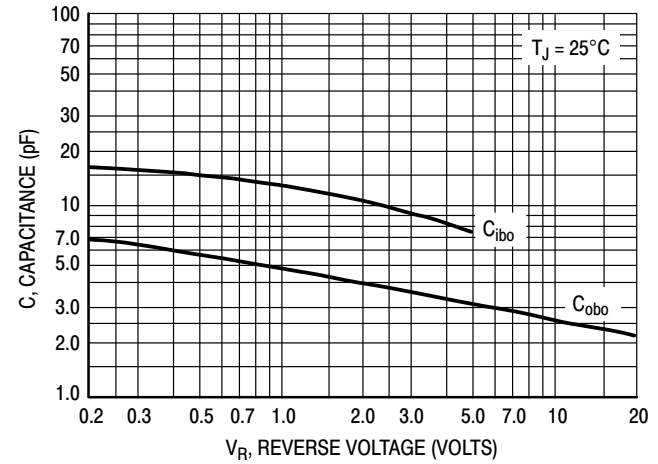
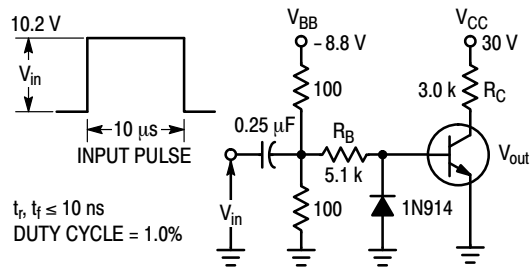


Figure 8. Capacitances



Values Shown are for I_C @ 10 mA

Figure 9. Switching Time Test Circuit

MMBT5550L, MMBT5551L

TYPICAL CHARACTERISTICS

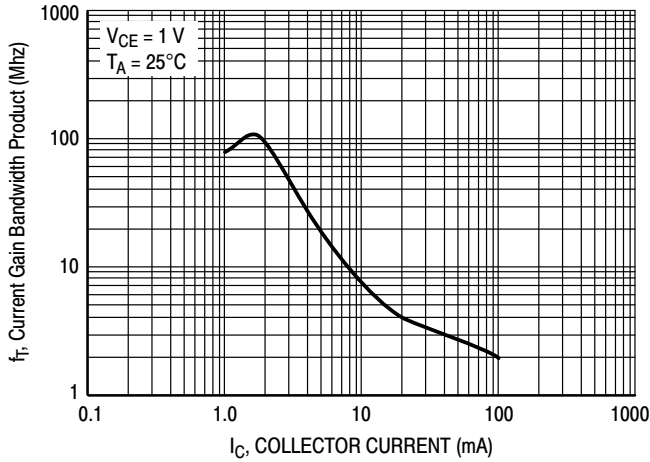


Figure 10. Current Gain Bandwidth Product

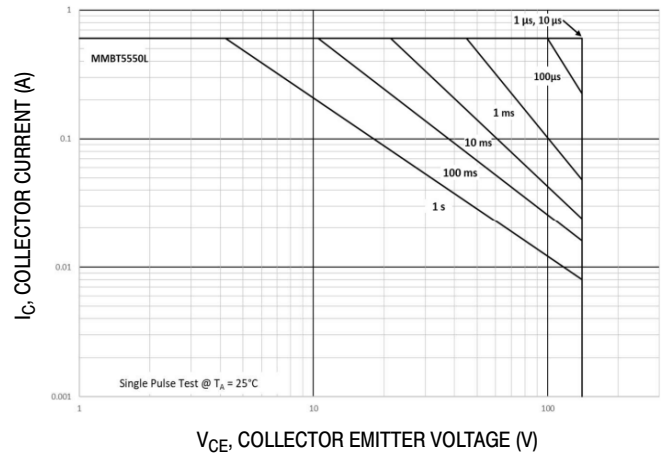
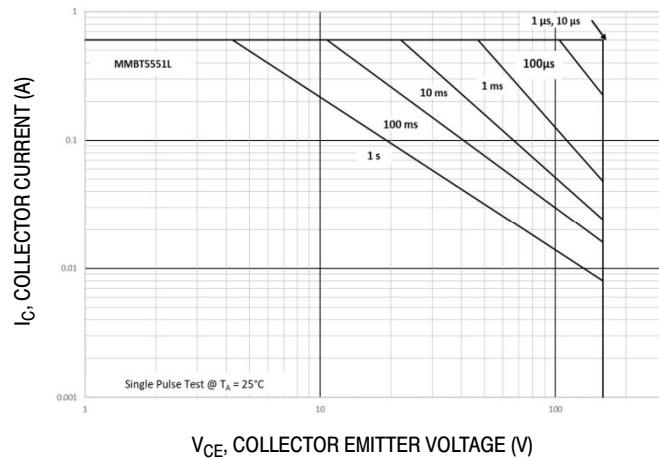


Figure 11. Safe Operating Area



V_{CE} , COLLECTOR EMITTER VOLTAGE (V)

Figure 12. Safe Operating Area

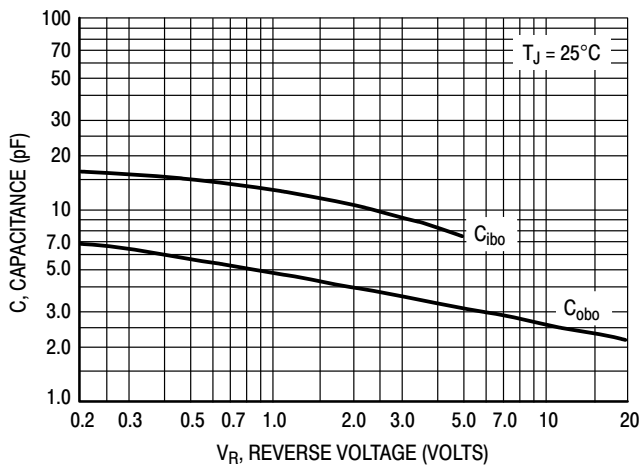


Figure 13. Capacitances

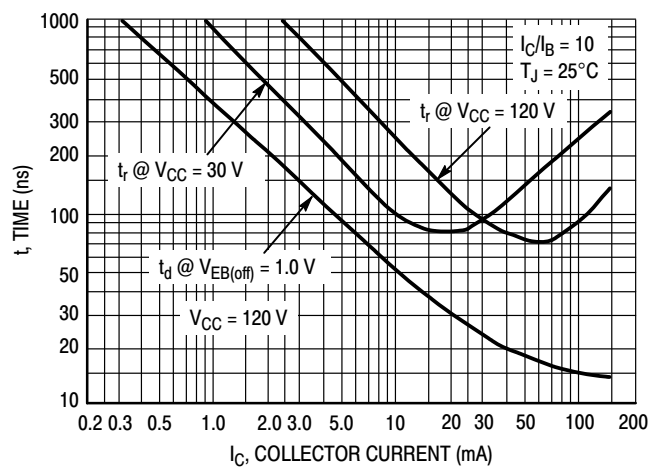


Figure 14. Turn-On Time



SCALE 4:1

SOT-23 (TO-236) 2.90x1.30x1.00 1.90P
CASE 318
ISSUE AU

DATE 14 AUG 2024



MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.89	1.00	1.11
A1	0.01	0.06	0.10
b	0.37	0.44	0.50
c	0.08	0.14	0.20
D	2.80	2.90	3.04
E	1.20	1.30	1.40
e	1.78	1.90	2.04
L	0.30	0.43	0.55
L1	0.35	0.54	0.69
HE	2.10	2.40	2.64
T	0°	---	10°

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSIONS: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

STYLES ON PAGE 2

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STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE		
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE	STYLE 19: PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE	STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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